IN THE CLAIMS:

Please cancel claim 11 and amend claims 1, 10, 19, 21, 31, 33, 43, and 44 as follows

B5 Sub C2

1. (Amended) A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by an anisotropic conductive film,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film, and

wherein a side surface of said metallic film is covered with a protecting film along the length direction of said lamination film.

B6 Sub C3

10. (Amended) A contact structure for electrically connecting a connecting wiring over a substrate to a wiring over another substrate by an anisotropic conductive film,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film,

wherein a side surface of said metallic film is covered with an insulating film along the length direction of said lamination film, and

wherein said metallic film is not in contact with said anisotropic conductive film.

B7 Sub C4

19. (Amended) A semiconductor device comprising:

a circuit comprising a thin film transistor over a substrate; and

a connecting wiring over said substrate for connecting said circuit to another circuit,

wherein said connecting wiring is a lamination film comprising a metallic film and a transparent conductive film in contact with said metallic film, and

wherein a side surface of said metallic film is covered with an insulating film along the length direction of said lamination film.

B8

21. (Amended) A semiconductor device of claims 19 wherein the connecting wiring is electrically connected to a wiring of said another substrate via an anisotropic conductive film.

31. (Amended) A semiconductor device comprising:

a first substrate comprising a circuit comprising a thin film transistor;

a second substrate opposing said first substrate;

a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit; and

an insulating film in contact with a side surface of said metallic film,

wherein said connecting wiring and said protecting film are formed over said first substrate and

wherein said protecting film is formed along with the length direction of said lamination film.

33. (Amended) A semiconductor device of claims 31 wherein said connecting wiring is electrically connected to a wiring of said second substrate via an anisotropic conductive film.

43. (Amended) A semiconductor device comprising:

a first substrate comprising a circuit comprising a thin film transistor;

a second substrate opposing said first substrate;

a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit;

a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and

a protecting film in contact with a side surface of said metallic film comprising the same material as that of the column-shape spacer,

wherein said connecting wiring, said column spacer, and said protecting turn are formed over said first substrate, and

wherein said protecting film is formed along with the length direction of said lamination film.

44. (Amended) A semiconductor device of claims 43 wherein said connecting wiring is electrically connected to a wiring of said second substrate via an anisotropic conductive film.

Please add new claims 54-56 as follows:

--54. A semiconductor device of claim 19 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

55. A semiconductor device of claim 31 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

56. A semiconductor device of claim 43 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.--